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# Characteristics of Interconnects on FR408 at Millimeter-Wave Frequencies

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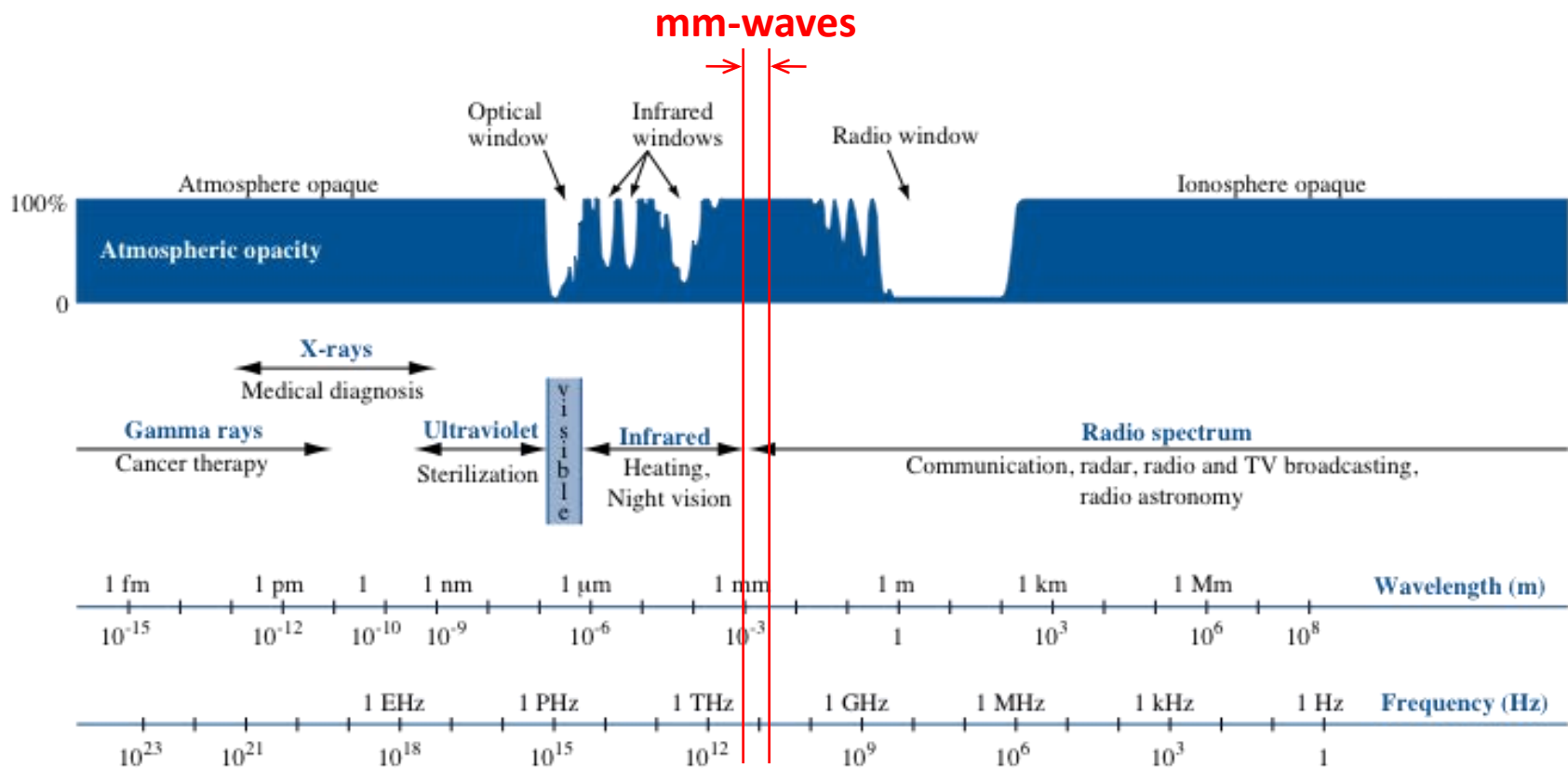
# Characteristics of Interconnects on FR408 at Millimeter-Wave Frequencies

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Rashaunda Henderson

*The University of Texas at Dallas*

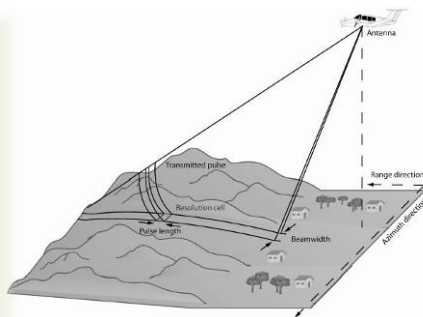
- Motivation
  - CMOS and Millimeter-Wave Applications
  - System-in-package solution
- Why FR408?
- Interconnect Design
  - Coplanar Waveguide (CPW)
  - Microstrip
- Fabrication
- Measurements and Results
  - CPW
  - Microstrip with measurement probe pads
- Summary of results
- Conclusion
- Future Work

- Millimeter (mm-wave) Frequencies (60GHz to 300GHz)
  - $\lambda = c/f$ 
    - 5mm at 60GHz, 1mm at 300GHz

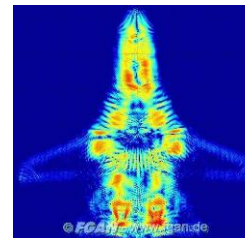




• UAV



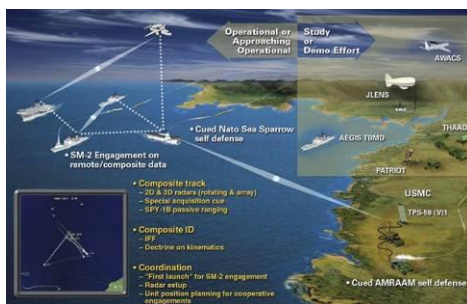
• Imaging



• Automotive Radar



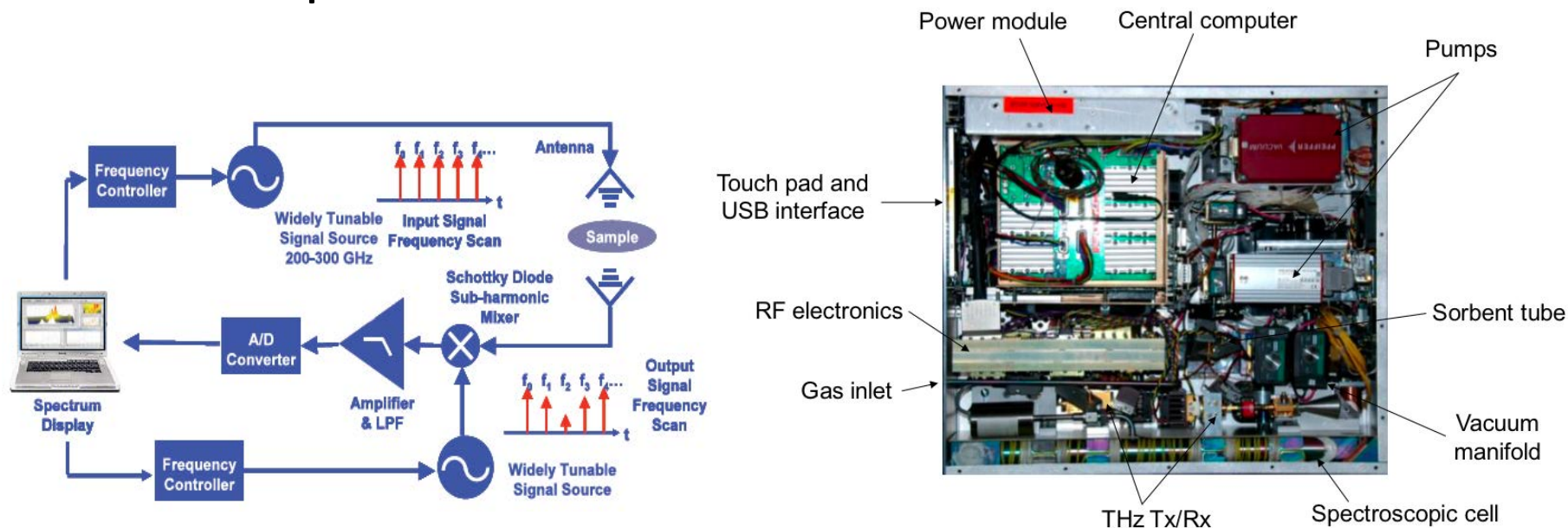
• Secured High Throughput Link



• Through wall surveillance



- CMOS and Millimeter-Wave Applications
  - Gas spectrometer- 180-300 GHz

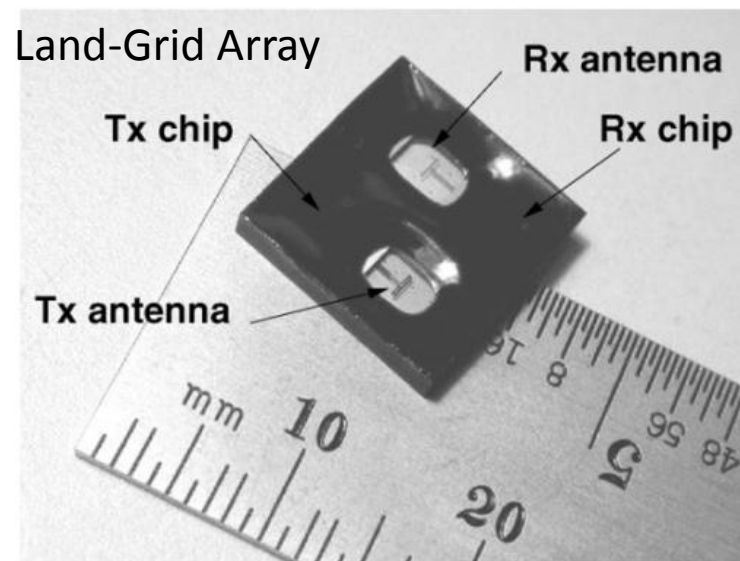
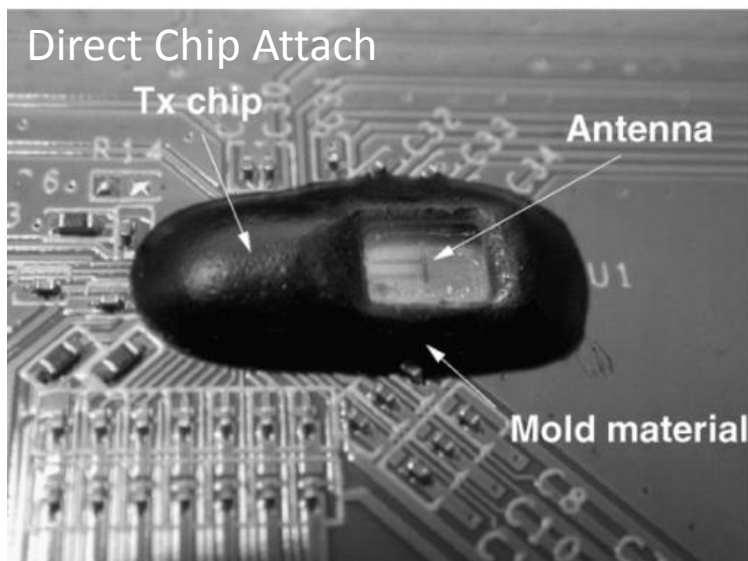


## Gas Spectrometer Currently Implemented with Waveguide and Horn Antennas

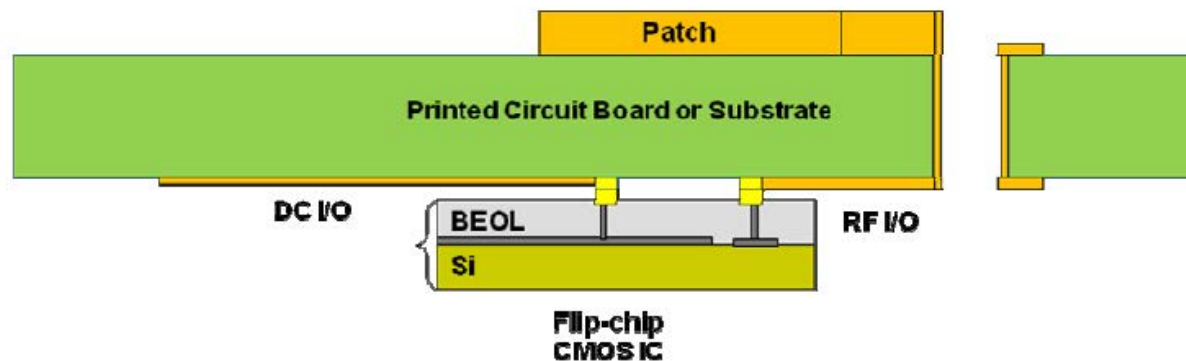
- System-in-package solution
  - FR408



60 GHz IBM Approach

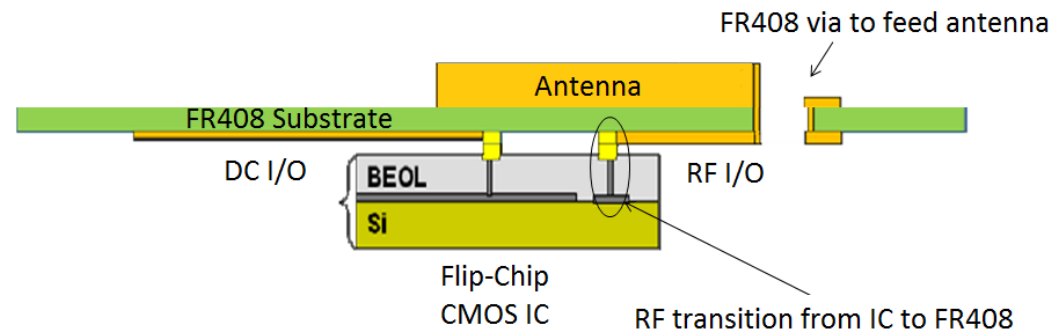


UTD Approach



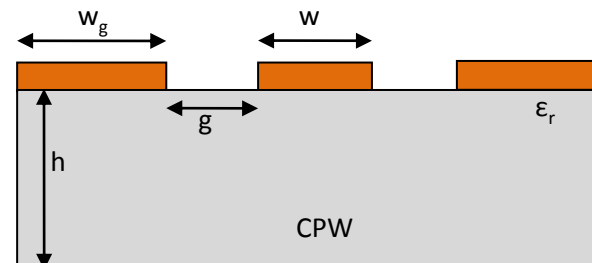
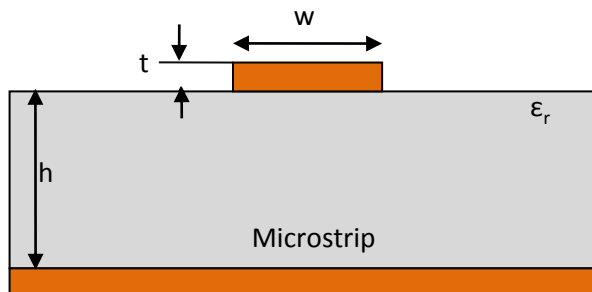


- Material – FR408
- Process development – Special etch technique to realize feature sizes needed for mm-wave
- Interconnect study – best performing
- Integration
  - Attach silicon die to FR408
  - Use vias or EM coupling to transfer signal to antenna



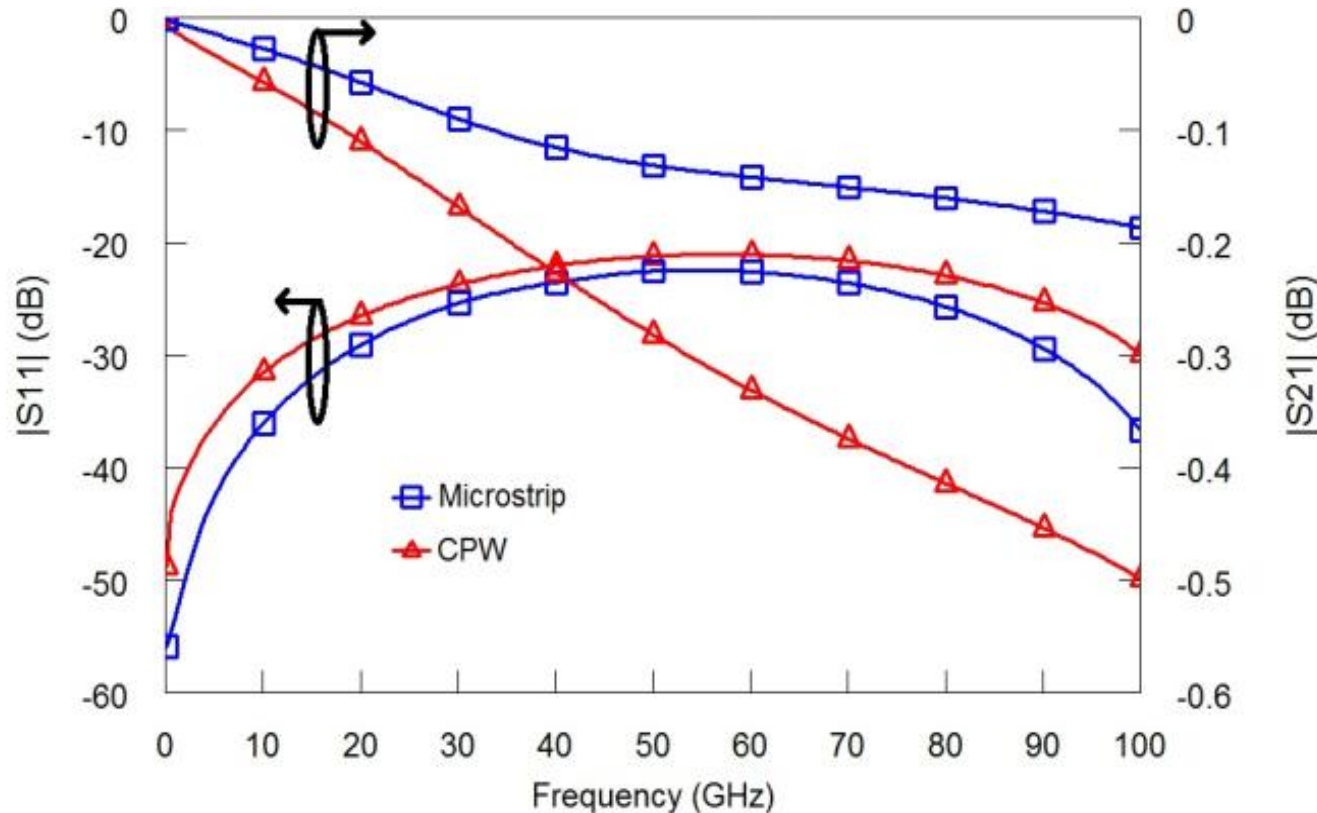
Substrate Material	Cost	Dielectric Constant	Loss tangent
FR4 G10 Laminate	X	4.2	0.02
FR408 Laminate	1.5X	3.65	0.013
RT Duroid 5880	20X	2.2	0.0009

- Low cost
- Better Performance
- Dielectric Thickness : 125  $\mu\text{m}$
- Copper Thickness: 17  $\mu\text{m}$ , double- sided
- Bulk Conductivity: 2.17 e-12 S/m



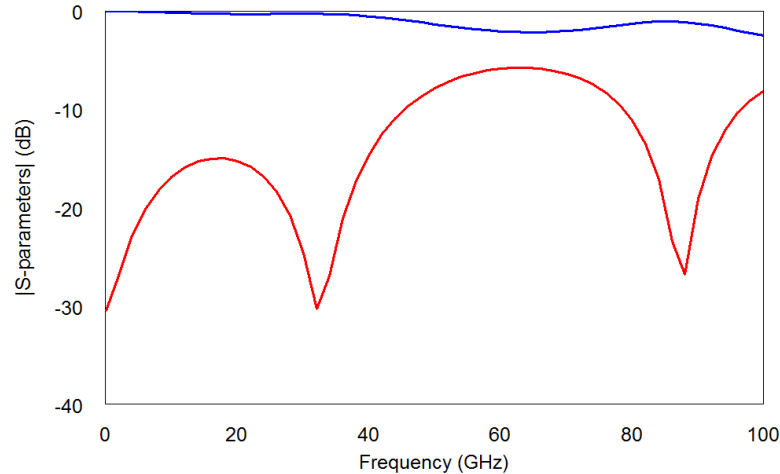
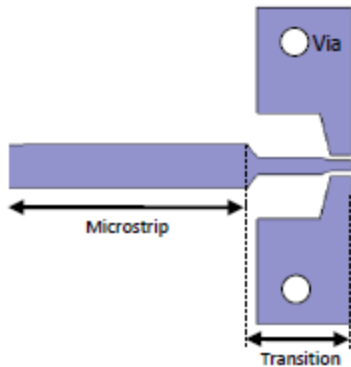
$$h = 125 \mu\text{m}; t = 17 \mu\text{m}; \epsilon_r = 3.65$$

TML	Width(w) ( $\mu\text{m}$ )	Gap (g) ( $\mu\text{m}$ )	$Z_0$ ( $\Omega$ )
Microstrip-1	264.5	-	50
Microstrip-2	273	-	49
CPW – 1	75	20	51
CPW – 2	140	25	50
CPW – 3	150	25	49
CPW – 4	45	15	50



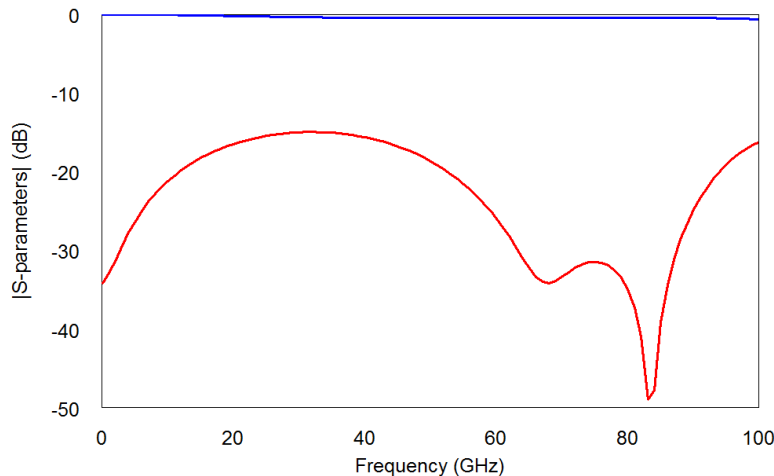
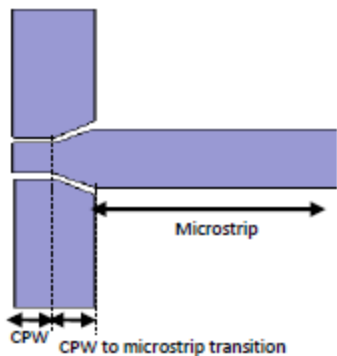
- HFSS simulated S-parameters for 50  $\Omega$  CPW-1 and microstrip-1 lines. Line length is 1mm.
- Return loss for both lines is comparable at below 20 dB.
- Insertion loss for CPW is greater than that of microstrip.

- Transition with vias to ground filled with epoxy.

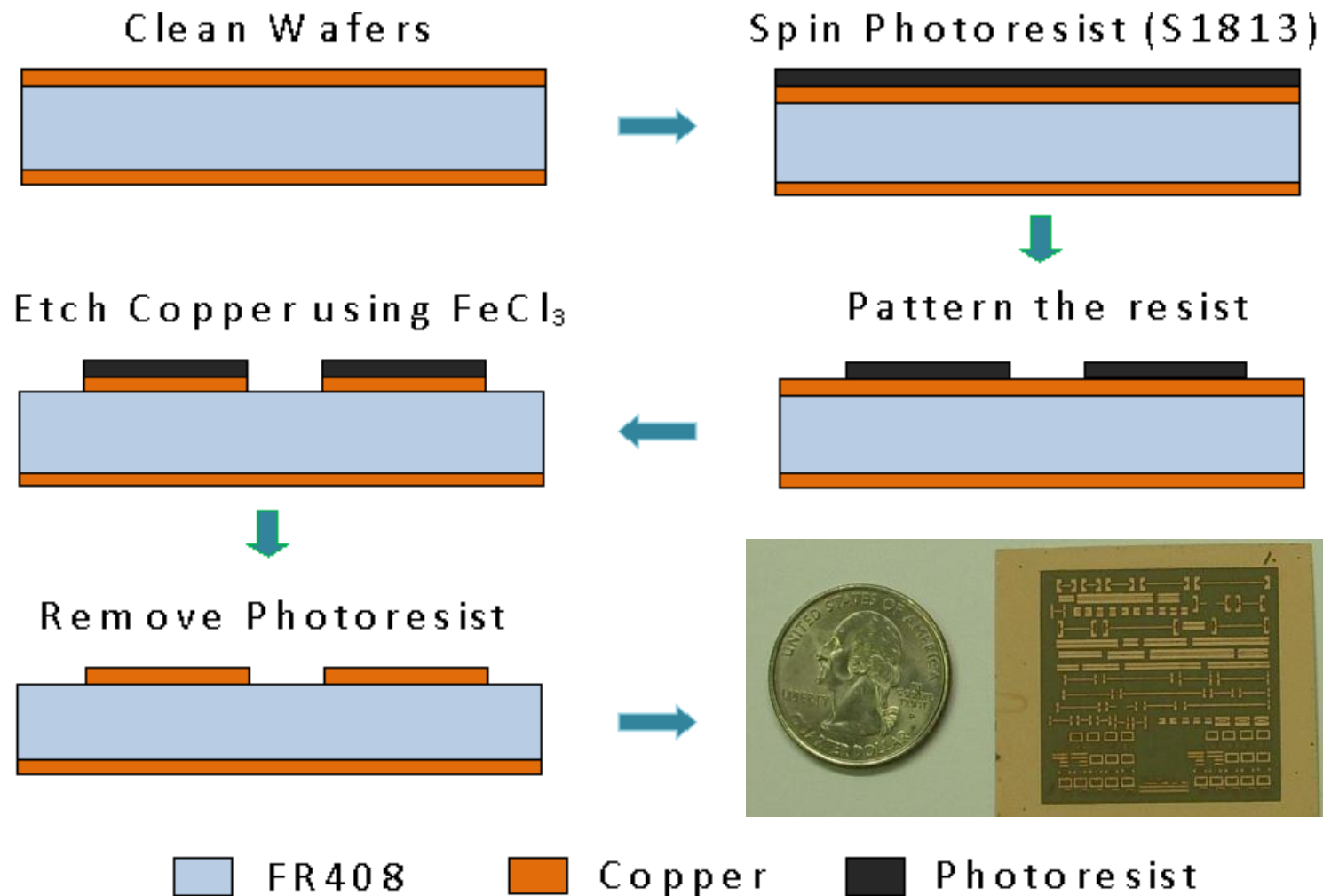


Total Length = 2 mm  
*Transition dimensions:*  
 Transition length = 500  $\mu\text{m}$   
 Via diameter = 150  $\mu\text{m}$   
*Microstrip dimensions:*  
 $w = 273 \mu\text{m}$   
 $l = 1 \text{ mm}$

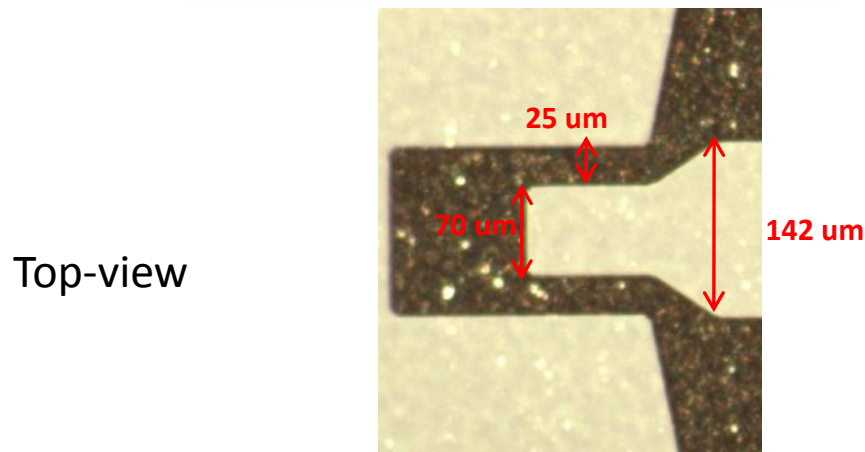
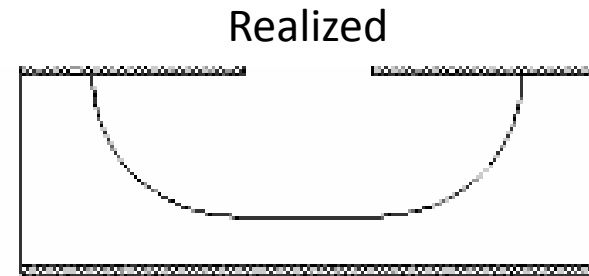
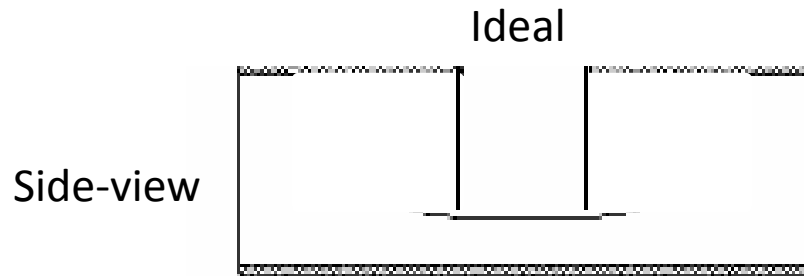
- Vialess transition based on [1].



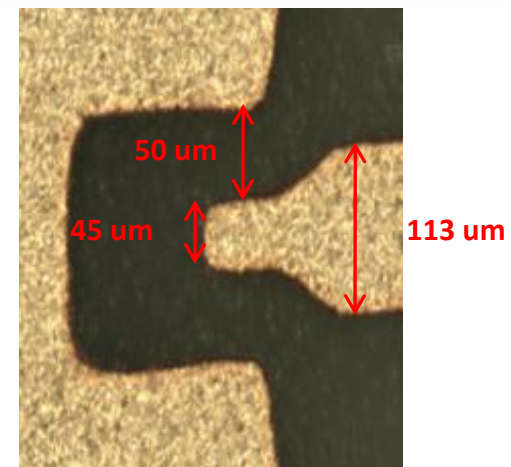
Total Length = 1.4 mm  
*CPW dimensions:*  
 $w = 140 \mu\text{m}$   
 $g = 25 \mu\text{m}$   
 CPW transition = 100  $\mu\text{m}$   
*Microstrip dimensions:*  
 $w = 264.5 \mu\text{m}$   
 $l = 1 \text{ mm}$



Isotropic wet etch causes undercut due to simultaneous horizontal and vertical etching.



Microstrip with epoxy transition  
before removing **photoresist** layer



Microstrip with epoxy transition  
after removing **photoresist** layer

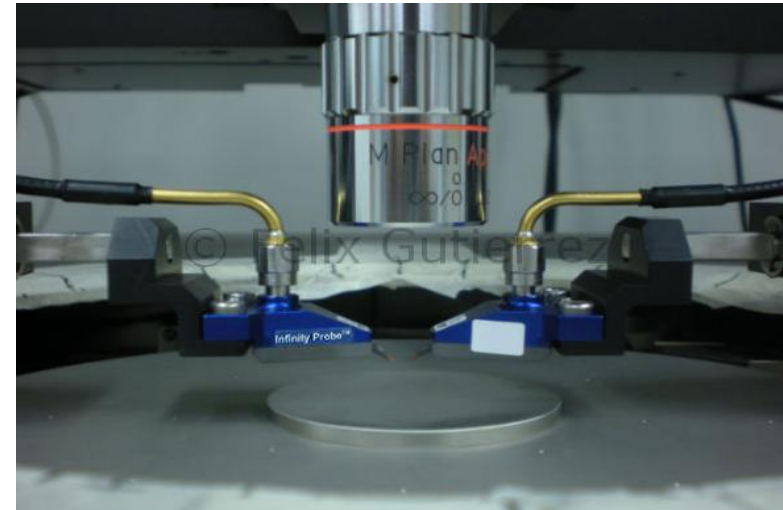


## Simulated Geometries      Fabricated Geometries

TML	Width ( $\mu\text{m}$ )	Gap ( $\mu\text{m}$ )	$Z_0$ ( $\Omega$ )	Width ( $\mu\text{m}$ )	Gap ( $\mu\text{m}$ )	$Z_0$ ( $\Omega$ )	$Z_0$ % diff
Microstrip-1	264.5	-	50	242.5	-	52.5	5 %
Microstrip-2	273	-	49	252	-	51.3	3 %
CPW – 1	75	20	51	60	40	70	37 %
CPW – 2	140	25	50	118	49	63	26 %
CPW – 3	150	25	49	135	40	54	10 %
CPW – 4	45	15	50	20	40	85	70 %

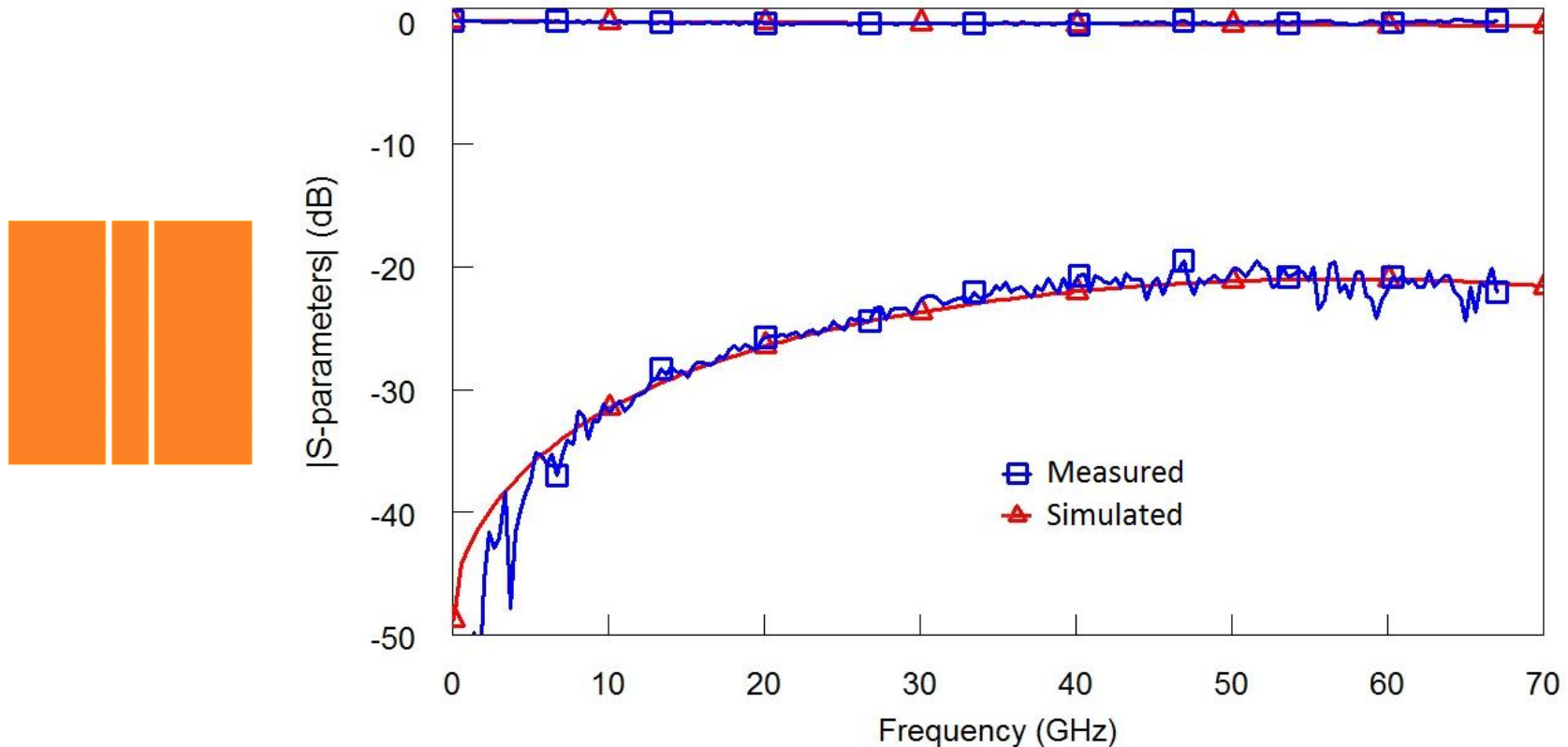
- Center line widths are narrower by 15-25  $\mu\text{m}$  and the gaps are 10-20  $\mu\text{m}$  wider
- Higher characteristic impedance

- Measurements up to 67 GHz
- Probe station with Agilent E8361A PNA



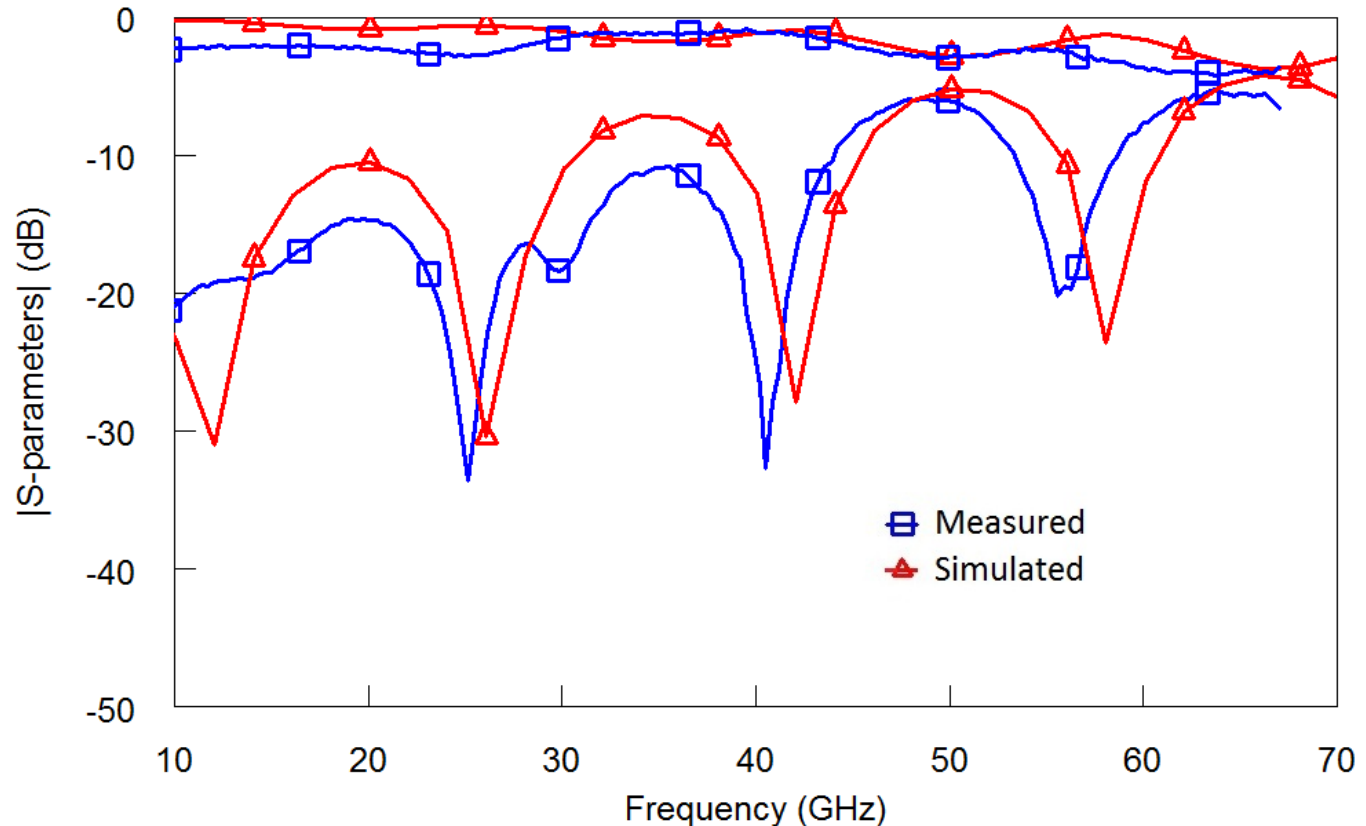
- Calibration type: 2-port SOLT
- Probes: GGB ground-signal-ground probes with 150  $\mu\text{m}$  pitch

## Measured vs. Simulated results for 1 mm long CPW-3 line



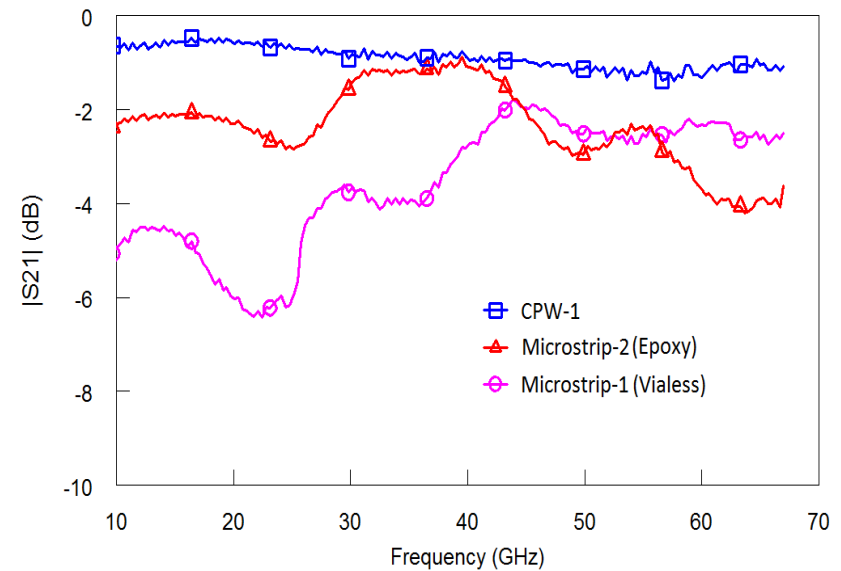
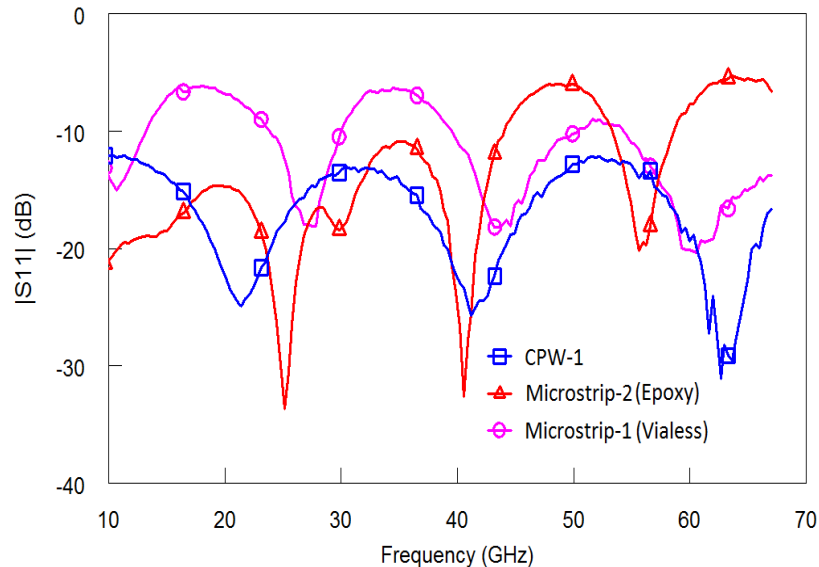
- Return loss of 20 dB or better and insertion loss of 0.27 dB or better.
- Good agreement between simulation and measurement.

Measured vs. Simulated results for 4.82 mm long microstrip



- 6 mils drill bit and silver epoxy used to create vias to ground.
- Simulation with fabricated geometry for microstrip-2 line.
- Good agreement between simulation and measurement.

## $|S_{11}|$ (dB) and $|S_{21}|$ (dB) for 4.82 mm long lines



### Loss/mm for FR408 lines at 60 GHz

Line	CPW-1	Vialess	Epoxy
$ S_{21} $ /mm (dB)	0.25	0.48	0.76
$Z_0 \Omega$	70	51.3	52.5

### Attenuation/mm for 50 $\Omega$ lines at 60 GHz

Line	GaAs	CMOS with p+ doping	CMOS with 8 $\mu\text{m}$ BCB layer	Duroid
Att./mm (dB)	0.09	1.6	0.96	0.07

- CPW and microstrip transmission lines have been simulated, fabricated and measured up to 67 GHz.
- Measured results show that CPW lines have an insertion loss of about 0.2 dB/mm.
- Microstrip line measurements suffer from transition effects. Measured results show that the vialess transition perform at higher frequencies.
- FR408 is a viable candidate for interconnects when short line lengths are utilized .

- Simulation – Extended study of CPW to microstrip transition design
- Design – Add de-embedding structures for microstrip
- Fabrication – Account for isotropic etch to improve realized geometries
- Measurement – Extend the frequency range and extract propagation and attenuation constant



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# Thank you.